

Wafer Support Apparatus for Electroplating Process and Method for Using the Same

5

ABSTRACT

A multi-layered wafer support apparatus is provided for performing an electroplating process on a semiconductor wafer ("wafer"). The multi-layered wafer support apparatus includes a bottom film layer and a top film layer. The bottom film layer includes a wafer placement area and a sacrificial anode surrounding the wafer placement area. The top film layer is defined to be placed over the bottom film layer. The top film layer includes an open region to be positioned over a surface of the wafer to be processed, i.e., electroplated. The top film layer provides a liquid seal between the top film layer and the wafer, about a periphery of the open region. The top film layer further includes first and second electrical circuits that are each defined to electrically contact a peripheral top surface of the wafer at diametrically opposed locations about the wafer.

[Fig. 5A]